Attorney Docket No. 5308-127DV PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Allen *et al.*
Serial No.: To Be Assigned
Filed: Concurrently Herewith
For: METHODS OF FABRICATING SILICON CARBIDE METAL-SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Date: November 12, 2003

Mail Stop PATENT APPLICATION
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a list of documents on form PTO-1449. Items 1-56 listed on the PTO-1449 were cited in parent application Serial No. 09/567,717, filed May 10, 2000. Since the benefit of this application is claimed under 35 U.S.C. §120, no copies need to be furnished in accordance with 37 C.F.R. §1.98(d); however, copies will be furnished on request. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. §1.56 and Section 609 of the MPEP.

No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Attorney Docket Number: 5308-127DV	Serial No.: TBA
	Applicants: Allen, et al.	
	Filing Date: Concurrently Herewith	Group:

U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1.	US2003/0075719	04/2003	Sriram	257	77	
	2.	6,316,793	11/2001	Sheppard et al.	257	103	
	3.	6,218,680	04/2002	Carter, Jr. et al.	257	77	
	4.	6,121,633	09/2000	Singh et al.	257	77	
	5.	6,107,649	08/2000	Zhao	257	138	
	6.	5,972,801	10/26/99	Lipkin, et al	438	770	
	7.	5,925,895	07/20/99	Sriram, et al.	257	77	
	8.	5,900,648	05/04/99	Harris et al.	257	77	
	9.	5,895,939	4/20/99	Ueno	254	279	
	10.	5,719,409	02/1998	Singh et al.	257	77	
	11.	5,686,737	11/1997	Allen	257	77	
	12.	5,510,630	04/1996	Agarwaa et al.	257	77	
	13.	5,399,883	3/21/95	Baliga	257	57	
	14.	5,396,085	03/07/95	Baliga	257	77	
	15.	5,229,625	04/20/93	Suzuki et al.	257	77	
	16.	5,270,554	12/14/93	Palmour	257	77	
	17.	5,264,713	11/1993	Palmour	257	77	
	18.	4,947,218	08/07/90	Edmond, et al.	357	13	
	19.	4,897,710	01/30/90	Suzuki et al	357	71	
	20.	4,762,806	08/09/88	Suzuki et al	437	100	
	21.	4,757,028	07/12/88	Kondoh et al.	437	40	
	22.	4,732,871	03/22/88	Buchmann et al.	437	41	
	23.	3,903,592	09/1975	Heckl	29	578	

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EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation Yes | No
	24.	EP19900169	07/1999	European			
	25.	EP0518683A	12/16/92	EPO			
	26.	JP 1-196873	08/1989	Japan, Fujii et al.			
	27.	JP 54-155482	10/29/79	Japanese Patent w/ Abridged Eng. Translation			
	28.	JP 59-134874	08/1984	Japan, Shimizu et			
	29.	JP1106476	04/24/89	Japanese Patent Abstract			
	30.	JP1106477	04/24/89	Japanese Patent Abstract			
	31.	JP1308876	12/13/89	Japanese Patent Abstract			
	32.	JP2-10772	01/16/90	Japanese Patent w/ Abridged Eng. Translation			
	33.	JP47-5124	03/15/72	Japanese Patent w/ Abridged Eng. Translation			
	34.	JP60-142568	02/27/85	Japanese Patent w/ Abridged Eng. Translation			
	35.	JP60-154674	08/14/85	Japanese Patent w/ Abridged Eng. Translation			
	36.	JP63047983	02/29/88	Japanese Patent Abstract			
	37.	JP9-36359	02/1997	Japan, Ueno			
	38.	WO 01/67521 A1	09/13/01	PCT	HO1L	29/872	Abstract
	39.	WO 01/86727 A2	11/15/01	PCT	HO1L	29/24	

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	40.	"A 10 W 2 GHz Silicon Carbide MESFET," *Microwave Journal.* (September 1999).
	41.	"First Silicon Carbide Microwave Power Products are Introduced," *Applied Microwave & Wireless.*
	42.	"SiC MESFET Drives PCS Base Stations," *Wireless Systems Design.* (October 1999).
	43.	Allen, et al. "Silicon Carbide MESFET's with 2 w/mm and 50% P.A.E. at 1.8 GHz," *MTT Conference.* 1996.
	44.	Browne, Editorial: *The Power and the Glory*, Microwaves & RF. July 1999, p. 17
	45.	Browne, Jack. "Top Products of 1999," *Microwaves &RF.* (December 1999).
	46.	Browne, *SiC MESFET Delivers 10-W Power at 2 GHZ*, Microwaves & RF. October 1999, pp. 138-139
	47.	Carter et al., *Silicon Carbide and Related Materials, 1999, Part 2, Materials Science Forum,* Vols. 338-342, pp. 1247-1266 (2000).
	48.	Evwaraye et al., *Examination of electrical and optical properties of vanadium in bulk n-type silicon carbide,* J. Appl. Phys. 76 (10), 1994.
	49.	Heftman, Gene, "Wireless Semi Technology Heads Into New Territory," *Microwaves & RF.* (February 2000).
	50.	Hilton et al., *Suppression of Instabilities in 4H-SiC Microwave MESFETs,* 2000 8th IEEE International Symposium.
	51.	Hilton et al., *Surface Induced Instabilities in 4H-SiC Microwave MESFETs*, Materials Science Forum, Vols. 338-342, 2000, pp. 1251-1254
	52.	Jonsson et al., *Physical Simulations on the Operations of 4H-SiC Microwave Power Transistors*, Materials Science Forum, Vols. 338-342, 2000, pp. 1263-1266
	53.	Kelner, et al. "β -SiC MESFET's and Buried-Gate JFET's," *IEEE Electron Device Letters.* Vol. EDL-8, No. 9, (Sept. 1987).
	54.	Kong, et al. "Temperature dependence of the current-voltage characteristics of metal-semiconductor field-effect transistors in *n*-type β -SiC grown via chemical vapor deposition," *Applied Physics Letters.* Vol. 5i, No. 5, (10 Aug. 1987).
	55.	Konstantinov et al., *Investigation of Lo-Hi-Lo and Delta-Doped Silicon Carbide Structures*, Mat. Res. Soc. Symp. Proc., Vol. 640, 2001, pp. H2.4.1-H2.4.6
	56.	Ma, et al., *High Efficiency LDMOS Power FET for Low Voltage Wireless Communications*, 1996 IEEE.
	57.	Nilsson et al., *Characterization of SiC MESFETs on Conducting Substrates*, Materials Science Forum, Vols. 338-342, 2000, pp. 1255-1258
	58.	Noblanc et al., *Power Density Comparison Between Microwave Power MESFET's Processed on Conductive and Semi-Insulating Wafer*, Materials Science Forum, Vols. 338-342, 2000, pp. 1247-1250

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	59.	Palmour, et al. "Characterization of device parameters in high-temperature metal-oxide-semiconductor field-effect transistors in β -SiC thin films," *Journal of Applied Physics*. Vol. 64, No. 4, (15 Aug. 1988).
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	62.	Rorsman et al., *Fabrication, Characterization and Modeling of SiC MESFETs*, Materials Science Forum, Vols. 338-342, 2000, pp. 12-59-1262
	63.	Soares, Robert. *GaAs MESFET Circuit Design*. pp. 7-9; 17-18, (1988).
	64.	Sriram, Saptharishi, U.S. Serial No. 10/165,672, filed October 24, 2001.
	65.	Sze, S.M., *Physics of Semiconductor Devices*. Chapter 6.4, pp. 341-347, (Date illegible).
	66.	Yokogawa et al., *Electronic Properties of Nitrogen Delta-Doped Silicon Carbide Layers*, Mat. Res. Soc. Symp. Proc., Vol. 640, 2001, pp. H2.5.1-H2.5.6
	67.	International Search Report of PCT/US 01/04957 filed February 15, 2001.
	68.	International Search Report of PCT/US 02/32204 dated February 26, 2003.

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